



Energy Materials Network
U.S. Department of Energy



HydroGEN
Advanced Water Splitting Materials

Novel Chalcopyrites for Advanced Photoelectrochemical Water-Splitting

Nicolas Gaillard
University of Hawaii

P162

This presentation does not contain any proprietary, confidential, or otherwise restricted information





Project Overview

Novel Chalcopyrites for Advanced Photoelectrochemical Water-Splitting

- Lead PI: Nicolas Gaillard (University of Hawaii)
- Co-PIs: Clemens Heske (UNLV)
Thomas Jaramillo (Stanford)

Award #	EE0008085
Start/End Date	10/01/2017 - 09/30/2020
Year 1 Funding*	\$280,172
Year 2 Funding*	\$430,570

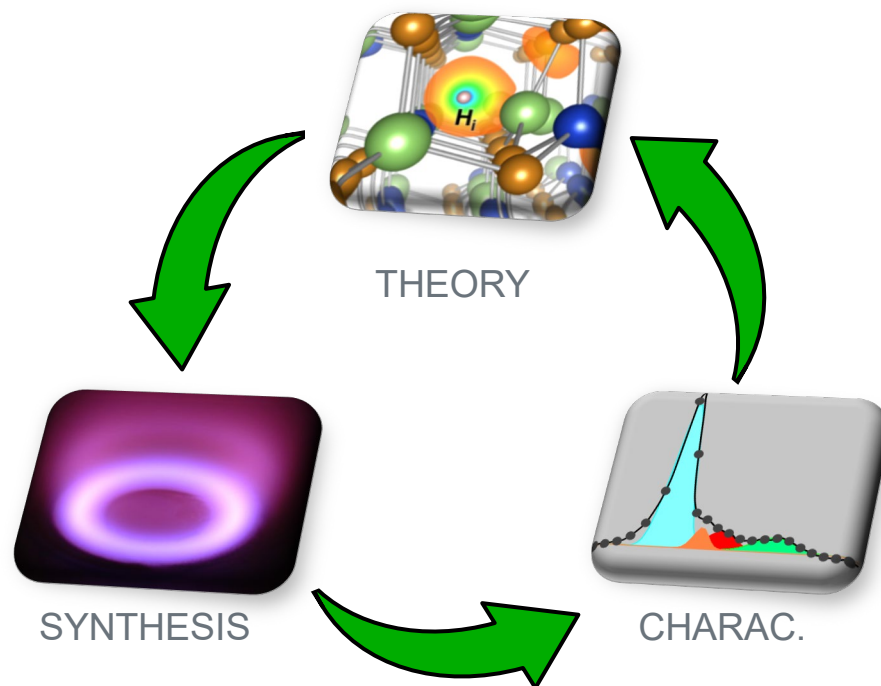
** this amount does not cover support for HydroGEN resources leveraged by the project (which is provided separately by DOE)*

Project Vision

We accelerate the development of new PEC water splitting materials through **integrated theory, synthesis and advanced characterization.**

Project Impact

We develop innovative techniques to fabricate chalcopyrite-based water splitting devices that can meet DOE's cost target of \$2/kg H₂.

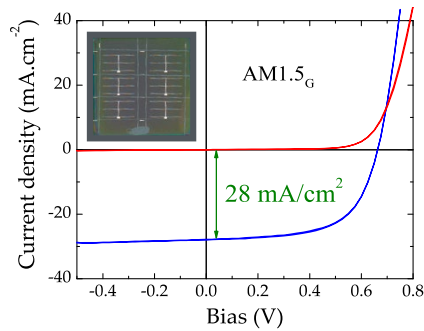




Approach – Technical background

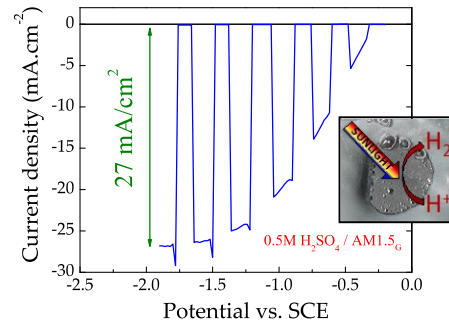
The promise of chalcopyrite-based PEC systems

1. Chalcopyrites can generate high photocurrent density



Solar cell

vs.



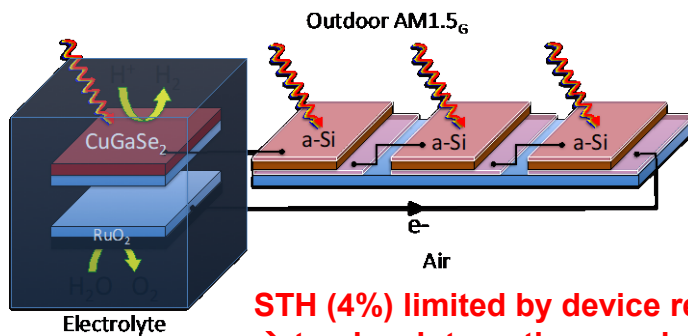
Photoelectrode

2. Low-cost processes available



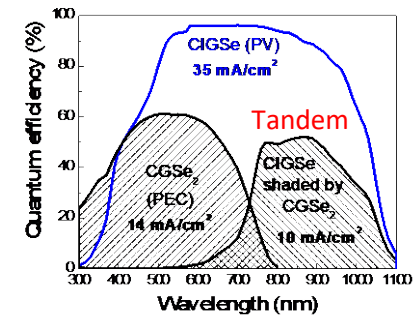
Chalcopyrite PV module cost: \$100/m²

3. Demonstrated water splitting with co-planar devices



STH (4%) limited by device real-estate:
→ tandem integration required.

4. Chalcopyrites are bandgap (E_g) tunable



Chalcopyrites compatible with tandem architecture

Take home message: chalcopyrites are excellent candidates for PEC water splitting. Novel wide bandgap (E_g) absorbers with improved optoelectronic properties needed for high efficiency **tandem cells**.



Approach – Summary

Project motivation

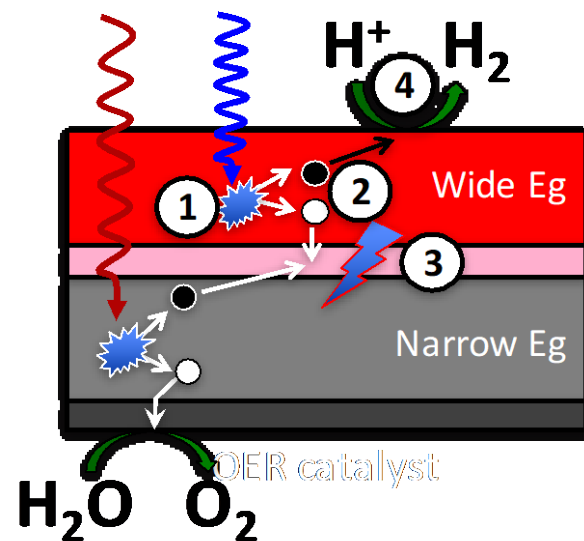
- UH/UNLV/Stanford/NREL/LLNL funded by EERE (2014) to identify promising chalcopyrites for water splitting H_2 production.
- New absorbers, interfaces and surface protection schemes were evaluated.
- Key barriers identified with these systems will be addressed in this new project.

Key Impact

Metric	State of the Art	Proposed
STH Efficiency	4%	>10%
Durability	350 hrs	>1,000 hrs

Technical barriers addressed in this project

- ① **Synthesis and Manufacturing barrier (AJ):** wide bandgap chalcopyrites are difficult to make with vacuum-based processes.
- ② **Materials Efficiency barrier (AE):** chalcopyrites interface energetics are not ideal for PEC water splitting.
- ③ **Integrated device configuration barrier (AG):** there is no known method to make efficient chalcopyrite-based tandems.
- ④ **Materials Durability barrier (AF):** coating ultra-thin protective layers on 'rough' polycrystalline chalcopyrites is challenging.





Approach – Partnerships / Scope

Integrated Theory, Analysis, Synthesis and Testing

Task 1 - Modeling and Synthesis of Chalcopyrite Photocathodes

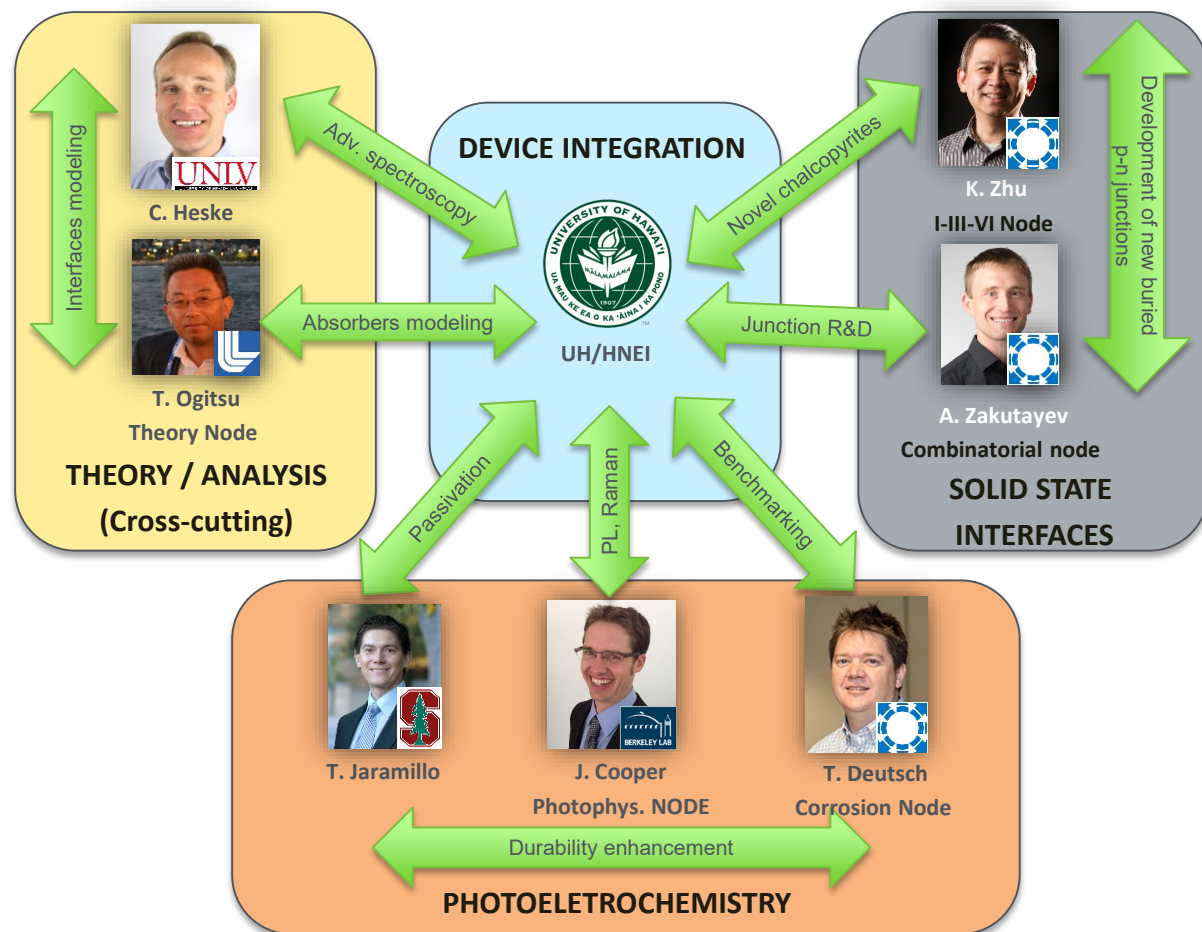
To address **Synthesis and Manufacturing (AJ)** and **Materials Efficiency (AE)** barriers, we model and develop new alloying and doping techniques to improve chalcopyrites efficiency.

Task 2 - Interfaces Engineering for Enhanced Efficiency and Durability

To address **Materials Efficiency (AE)** and **Materials Durability (AF)** barriers, we develop new interfaces to tune chalcopyrite “energetics” and improve their stabilities during PEC water splitting.

Task 3 - Hybrid Photoelectrode Device Integration

To address **Integrated device configuration barrier (AG)**, we develop a unique “transfer” method to create semi-monolithic chalcopyrite-based tandem devices.



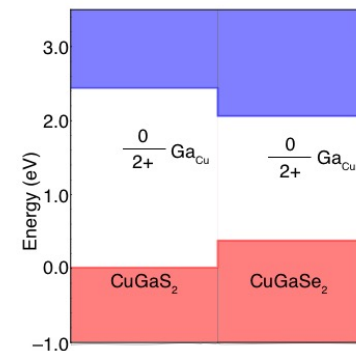
Take home message: our program is developing materials, methods and models addressing all fundamentals of photoelectrochemistry to accelerate the development of water splitting materials.



Approach – Innovation highlight #1

1) Novel chalcopyrites alloying using printing techniques

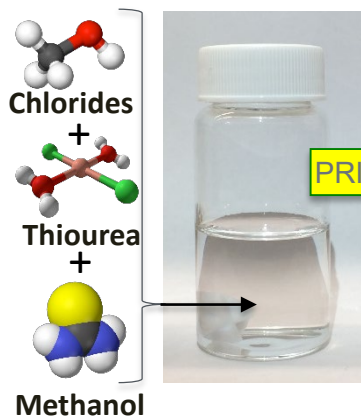
Synthesis and Manufacturing barrier (AJ): our models revealed that low photovoltage in CuInGaS_2 originates from Ga_{Cu} defects. Alternative Ga-free wide bandgap $\text{Cu}(\text{In},\text{Al})\text{Se}_2$, $\text{Cu}(\text{In},\text{B})\text{Se}_2$ identified by theory. However, these materials are too challenging to make by co-evaporation.



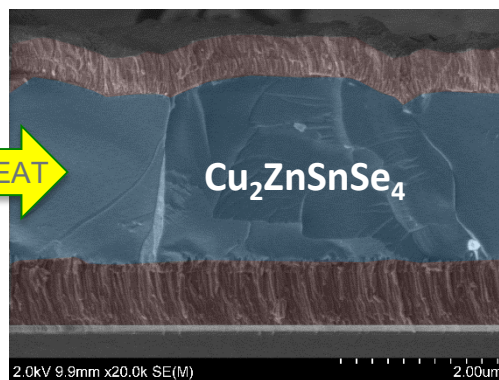
Proposed innovation: replace evaporation with “printing” technique to synthesize $\text{Cu}(\text{In},\text{Al},\text{B})\text{Se}_2$ using molecular inks containing all necessary constituents (e.g. CuCl , InCl_2 , $\text{AlCl}_3/\text{BCl}_3$).

→ **Proof of concept:** solution processed $\text{Cu}_2\text{ZnSnSe}_4$ solar cells (funding agency: ONR)

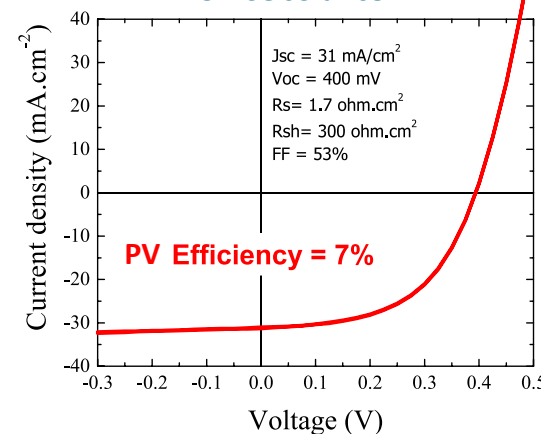
Molecular ink
(stable over 12 months)



Cross-section of a printed
CZTSe solar absorber



Current vs. voltage of a printed
CZTSe solar cell



→ **This approach lowers material cost and provides a viable path to meet DOE’s target of \$60/m².**



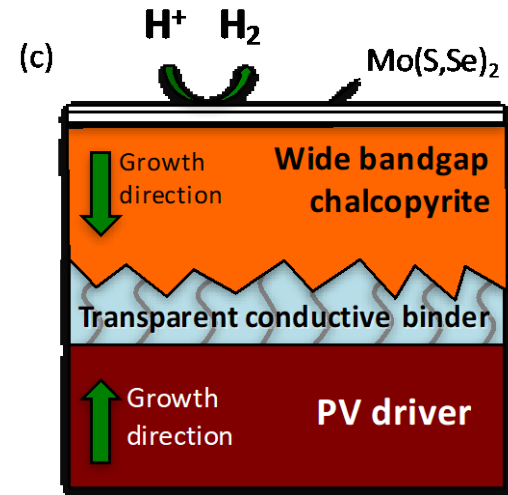
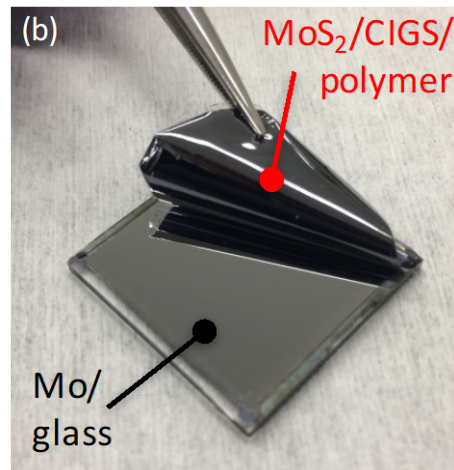
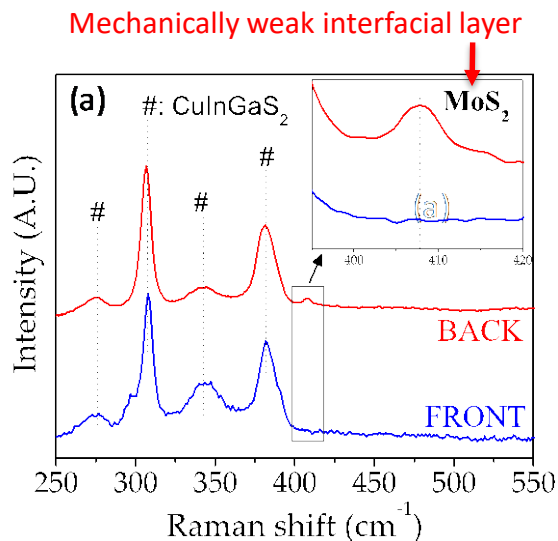
Approach – Innovation highlight #2

2) Innovative tandem device integration schemes

Integrated Device Configurations barrier (AG): materials compatibility (e.g. temperature) is the biggest challenge in multi-junction device integration. With current chalcopyrite PV technology, it is impossible to fabricate high efficiency monolithic multi-junction devices by directly depositing a wide-bandgap photocathode onto a narrow bandgap PV driver.

Proposed innovation: exfoliation of finished PEC cells and bonding onto fully processed PV drivers to create a semi-monolithic tandem device.

→ **Proof of concept:** 1 μm thick CIGS layer successfully “peeled” from substrate using polymer



→ **Enable integration of chalcopyrites into low-cost tandem water splitting devices**



Relevance & Impact – Leveraging EMN capability nodes

▶ Computational Materials Diagnostics and Optimization (T. Ogitsu).

- **Role:** modeling of materials optoelectronic properties (Eg vs composition, defects chemistry...etc).
- **Benefit to this program:** defines synthesis conditions and thermodynamic stability of novel chalcopyrites.
- **Broader impact for HydroGEN:** LLNL models can be used to predict bulk/interfaces of future materials for PEC water splitting and other H₂ production pathways.

▶ I-III-VI Compound Semiconductors for Water-Splitting (K. Zhu)

- **Role:** synthesis of high-purity PEC and PV chalcopyrite materials (CuGa₃Se₅ and CuInGaSe₂).
- **Benefit to this program:** “reference” vacuum-based chalcopyrites to evaluate new strategies (Na doping).
- **Broader impact for HydroGEN:** materials developed could be used for other H₂ production pathways (i.e. PV/electrolysis).

▶ High-Throughput Thin Film Combinatorial Capabilities (A. Zakutayev)

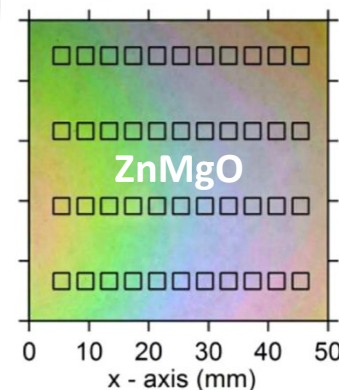
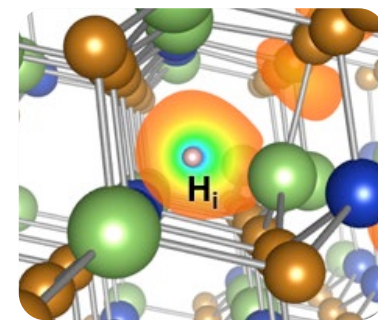
- **Role:** screening of n-type buffer materials (e.g. graded MgZnO: 40 ≠ compositions on 1 CIGS sample).
- **Benefit to this program:** accelerates material discovery for improved interface energetics (buried junction).
- **Broader impact for HydroGEN:** comprehensive library of optical, electronic and microstructural properties of new multi-compound materials made available to the scientific community via the HydroGEN Datahub.

▶ Corrosion Analysis of Materials (T. Deutsch)

- **Role:** supports development of surface passivation against photo-corrosion.
- **Benefit to this program:** provide access to unique instrumentation (e.g. ICPMS).
- **Broader impact for HydroGEN:** assessment of durability test protocols (e.g. fixed current vs. fixed potential).

▶ Photophysical Characterization of PEC Materials and Assemblies (J. Cooper)

- **Role:** supports development of novel wide-bandgap absorbers.
- **Benefit to this program:** provide new insights into charge carrier dynamics at Solid/Solid and Solid/Liquid interfaces.
- **Broader impact for HydroGEN:** identify corrosion mechanisms and potential pitfalls of protection strategies.





Accomplishments – Milestones and Go/No-Go criteria for budget period 2

→ Milestones and Go/NoGo decision points met or on track for Y2

Task #	Subtask Title	Milestone ID	Description	Anticipated Quarter	Status
2.1	Interface: energetics	Milestone #1	Determine the factors contributing to increased open circuit voltage of at least 900 mV with a MgZnO:Ga-coated and surface-treated wide bandgap chalcopyrite absorbers under simulated AM1.5G illumination, with a stretch goal of demonstrating over 200 mV improvement over the baseline by the end of year 2.	Q1	100%
2.2	Synthesis of chalcopyrite	Milestone #2	A printed polycrystalline Cu(In,Al,B)Se ₂ thin film material losing less than 50% of photocurrent and photovoltage after exfoliation/transfer.	Q2	100%
2.2	Interface: durability	Milestone #3	Retain 90% of metal content in a thin, transparent protective coating over the course of 100 hrs of electrocatalytic HER testing at -10 mA/cm ² .	Q3	90%
2.2	Interface: durability	Go/No-Go #1/2	Using a chalcopyrite photocathode, sustain hydrogen production (initially exceeding -8 mA/cm ²) at 90% of initial photocurrent density for 200 hours.	Q4	100%
3.2	HPE integration	Go/No-Go #2/2	Create a semi-monolithic tandem device exhibiting a Voc that is at least 50% of the sum of the Voc's of the individual tandems.	Q4	100%



Accomplishments – Task 1: Modeling and Synthesis of Chalcopyrite Photocathodes

Material barrier (AJ)

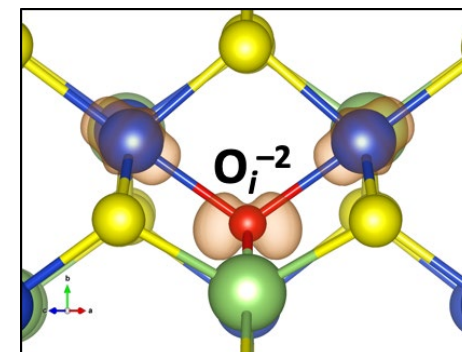
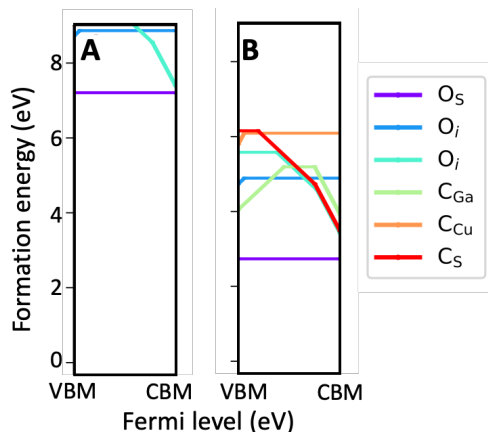
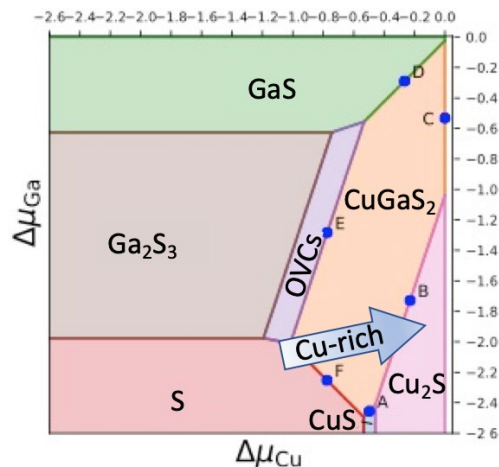
1.1) Theoretical modeling (LLNL theory node)

This year's focus: understanding influence of impurities on absorbers optical absorption losses

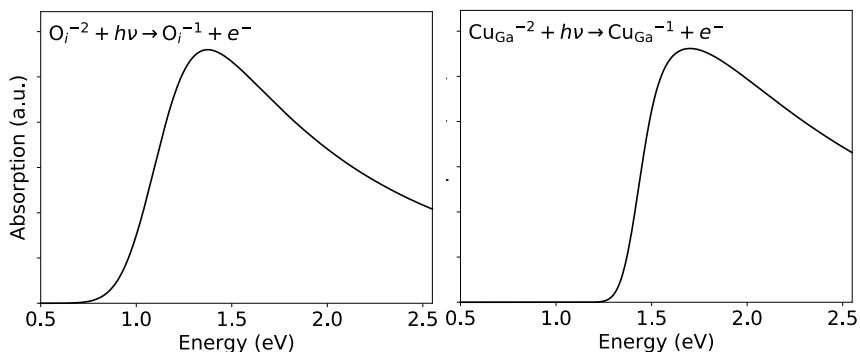
Higher O and C incorporation predicted in certain Cu-rich growth conditions

Illumination and interfacial band bending can influence the favorable defect populations

Charge density isosurface associated with localize state of O_i acceptors



Identifying (intrinsic and extrinsic) sources for sub-bandgap absorption losses



Broader impact to community: modeling provides critical information on absorbers thermodynamic stability, defect chemistry and helps identify promising new material candidates.



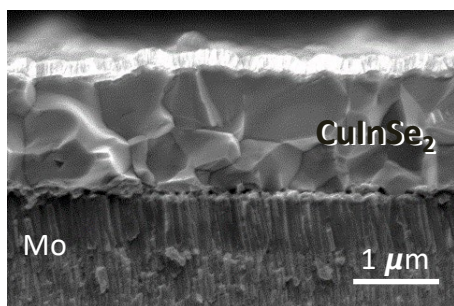
Accomplishments – Task 1: Modeling and Synthesis of Chalcopyrite Photocathodes

Material barrier (AJ)

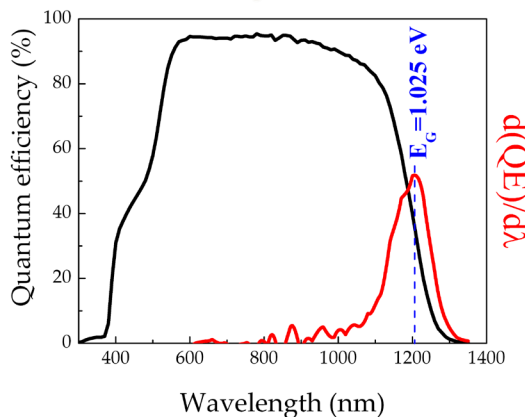
1.2) Chalcopyrites “printing” using molecular inks

a. Narrow bandgap CuInSe₂ (AMR 2019)

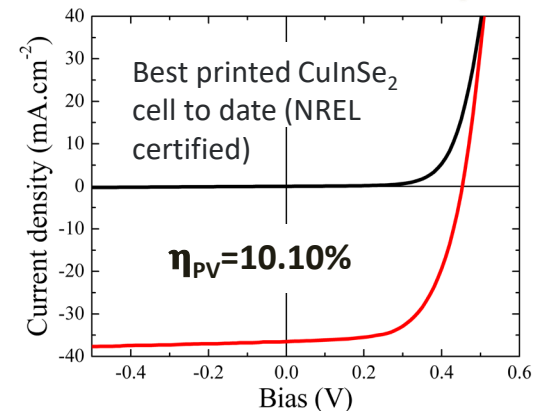
Highly crystalline printed CuInSe₂ absorber



Quantum efficiency >90% demonstrated

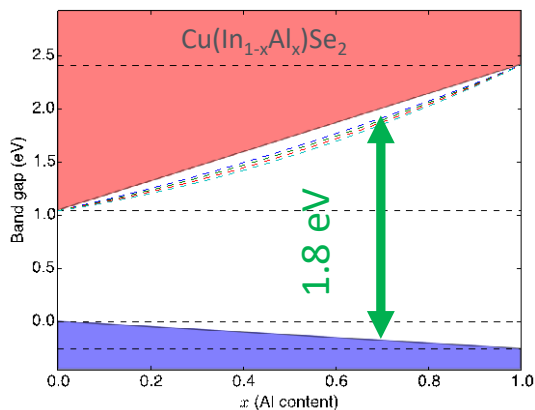


PCE >10% validated on PV cells by NREL

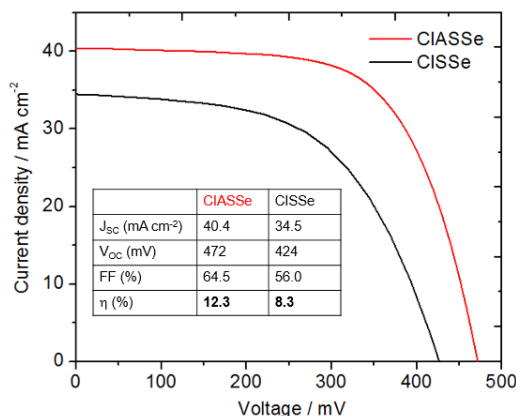


b. Wide bandgap CuInAlSe₂

Modeling of CIASe Eg vs. [Al] (LLNL)

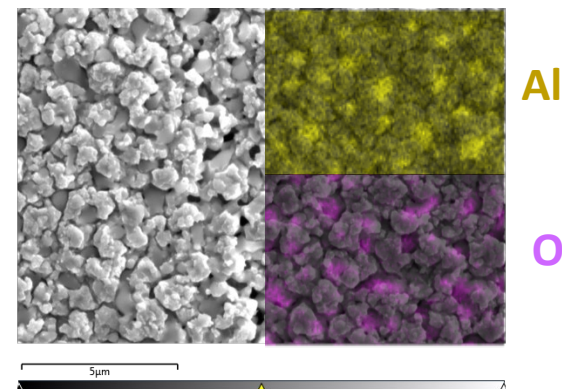


PCE >12% with CuInAlSe₂ ([Al]=10%)



	CIASe	CISSe
J _{sc} (mA cm ⁻²)	40.4	34.5
V _{oc} (mV)	472	424
FF (%)	64.5	56.0
η (%)	12.3	8.3

Challenge: Increasing [Al] beyond 30% leads to segregation (formation of Al₂O₃)



SEM top view / EDX map of CuInAlSe₂

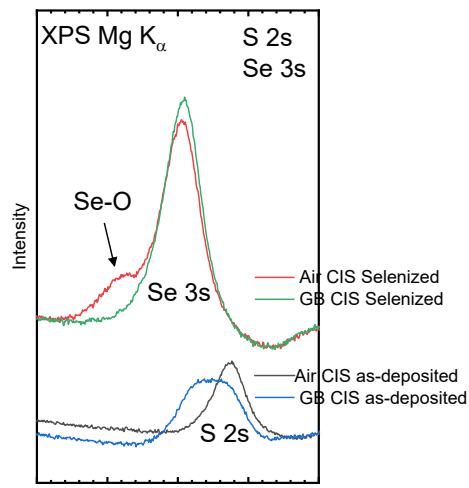
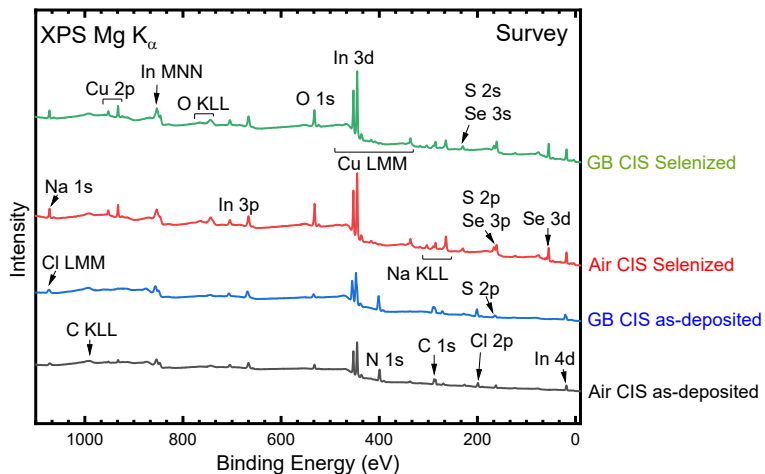


Accomplishments – Task 1: Modeling and Synthesis of Chalcopyrite Photocathodes

Material barrier (AJ)

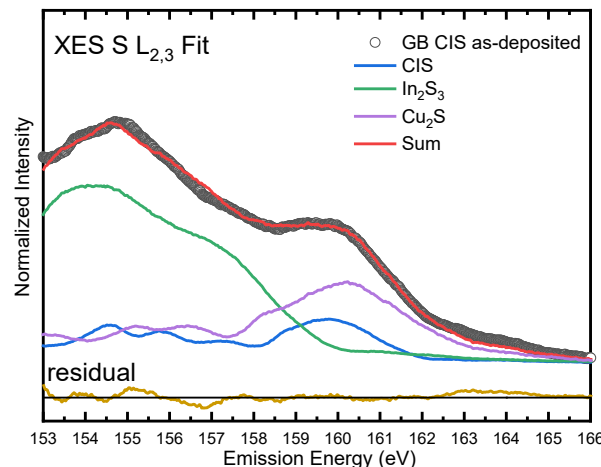
1.2) Effect of synthesis and coating environments: air and glovebox (GB)

X-ray Photoelectron Spectroscopy (XPS) @ UNLV

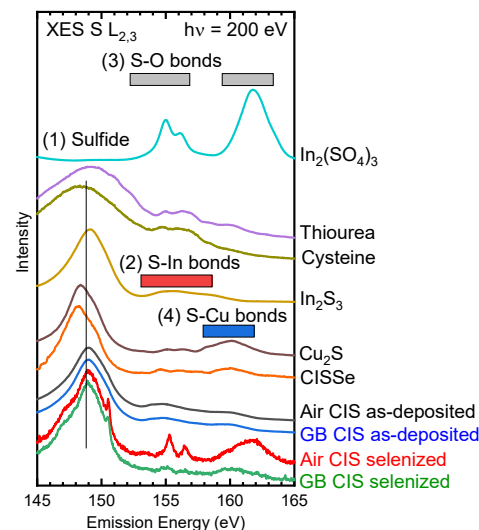


- Synthesis and spin-coating **in air**: more pronounced surface oxidation
- Synthesis and spin-coating **in GB**: less homogeneous, different chemical environments
- Selenization replaces majority of S atoms by Se
- Selenization also removes N and Cl, leads to presence of Na and increase of O

X-ray Emission Spectroscopy (XES) @ ALS



Fit analysis of glove-box (GB) $\text{CuIn}(\text{S}, \text{Se})_2$ sample using In_2S_3 , Cu_2S , and CuInS_2 (CIS) references: provides insights into the chemical impact of deposition and processing steps



- Local chemical environment of S at/near the surface
- As-deposited samples show a variety of local chemical bonding environments
- Increase in S-O bonds in absorber synthesized and spin-coated in air



Accomplishments – Task 2: Interfaces for Enhanced Efficiency & Durability

Efficiency
barrier (AE)

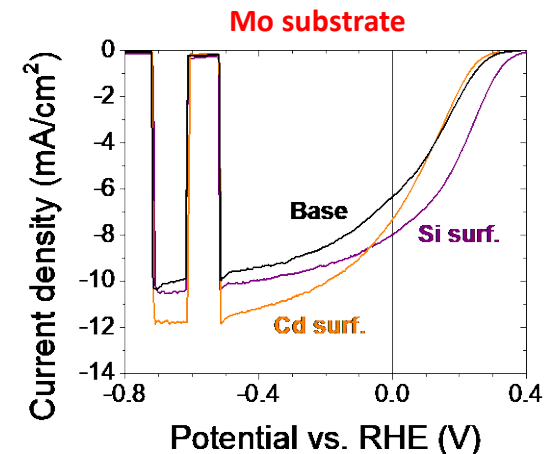
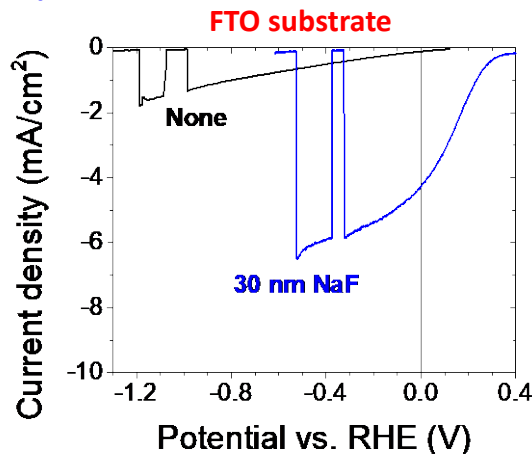
2.1) Surface treatment of CuGa_3Se_5 photocathodes (NREL CIGSe node)

a. Surface passivation with Na, Cd or Si (AMR 2019)

Surface treatments tested so far:

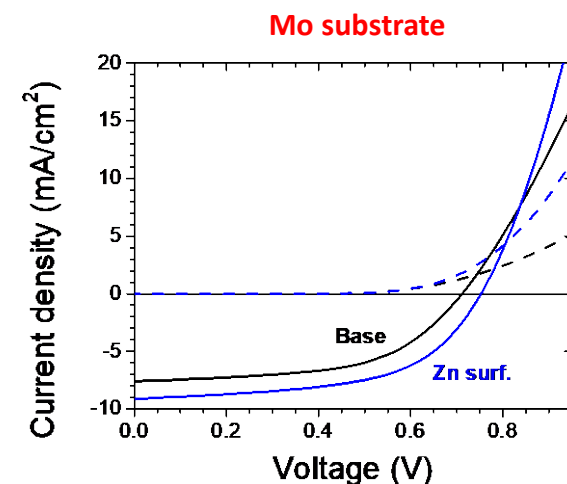
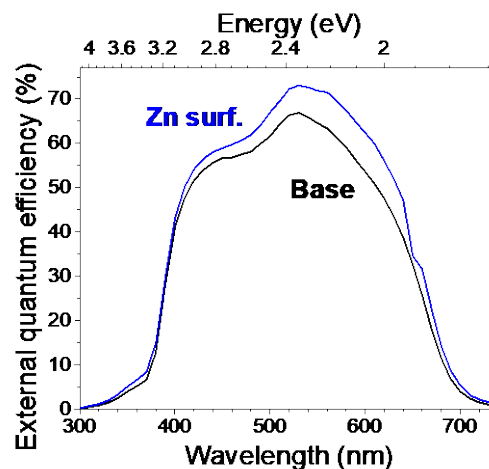
- NaF: 30 nm (evaporated)
- Si: 6 nm (evaporated)
- Cd²⁺: partial electrolyte (PE) treatment

→ Significant improvements in photoconversion (Na, Cd) and/or charge separation (Na, Si) achieved via surface treatment.



b. Surface passivation with Zn

- ▶ In situ Zn + Se co-evaporation at the end of CuGa_3Se_5 co-evaporation
- ▶ Zn surface treatment increases solar cell efficiency from 3.0 to 3.8%
- ▶ Improvements possibly due to surface passivation
 - $\text{CuGa}_3\text{Se}_5/\text{CdS}$ lattice mismatch is 5.3%
 - $\text{CuGa}_3\text{Se}_5/\text{ZnSe}$ lattice mismatch is 2.7%
- ▶ PEC photocathode performance degraded in H_2SO_4 electrolyte. Future tests to include higher pH.





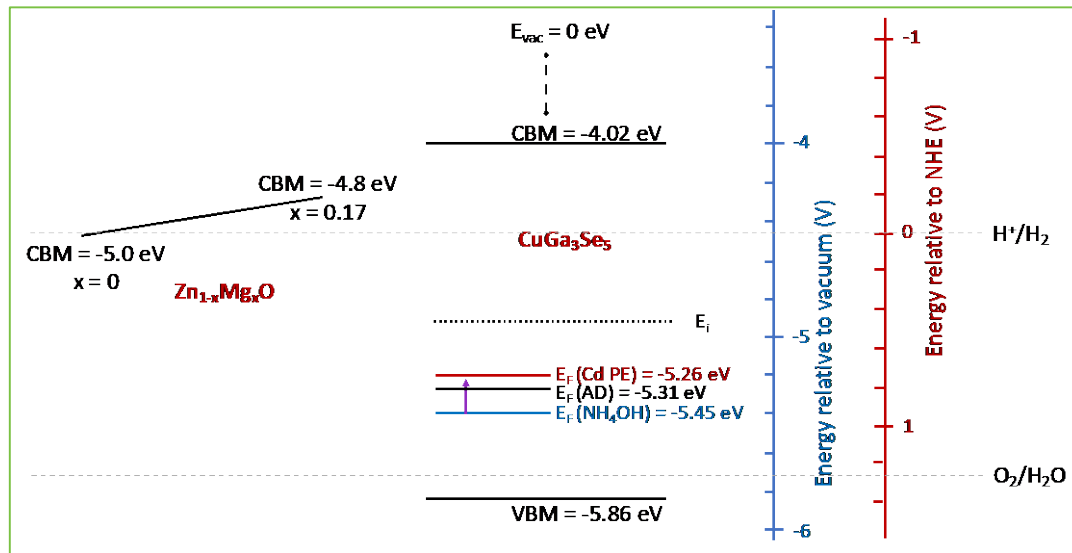
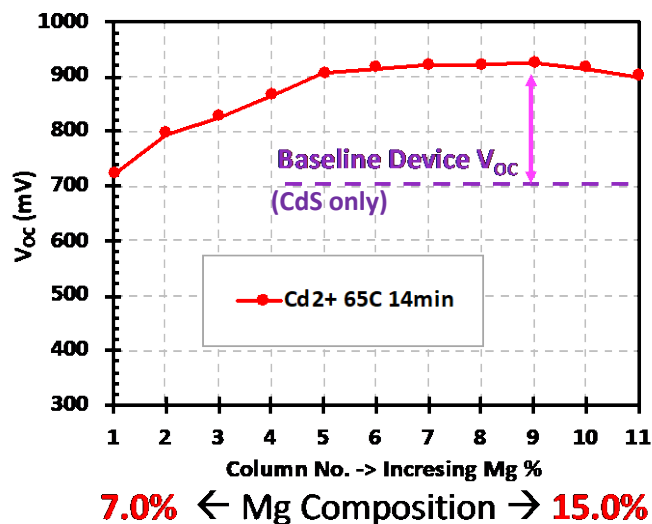
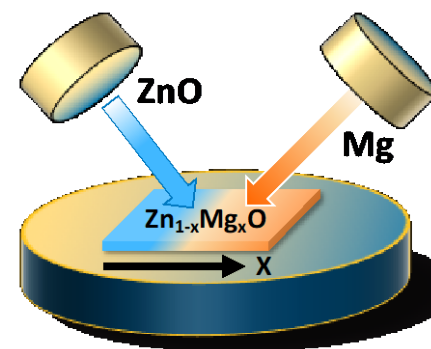
Accomplishments – Task 2: Interfaces for Enhanced Efficiency & Durability

Efficiency barrier (AE)

2.2) Combinatorial development of tunable “buffers” (NREL Combi./CIGSe Nodes)

Factors contributing to increased V_{OC} up to 925 mV with MZO and surface-treated $CuGa_3Se_5$ absorbers:

- Cd^{2+} partial electrolyte treatment
 - removes surface O and Na
 - Ion exchange of Cu and Ga with Cd; possibly create compensating defect(s)
 - Change of absorber surface conductivity type to either intrinsic or n-type (‘p-i-n’ junction)
- Improved CB alignment with higher bandgap $Mg_xZn_{1-x}O$



Energy band positions for $CuGa_3Se_5$ absorber with different surface treatments, in comparison with the CBM position in $Mg_xZn_{1-x}O$.

(based on XPS, Kelvin probe, hall effect and UV-Vis spectroscopy data, all measured at NREL)



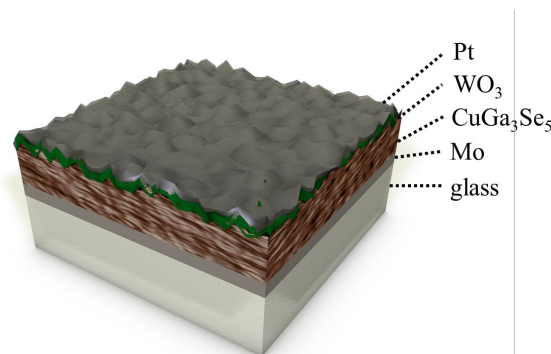
Accomplishments – Task 2: Interfaces for Enhanced Efficiency & Durability

Durability barrier (AF)

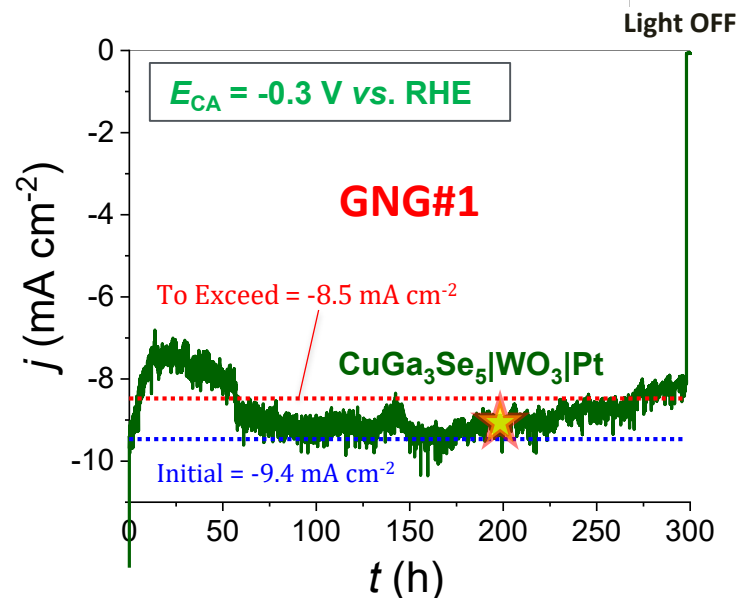
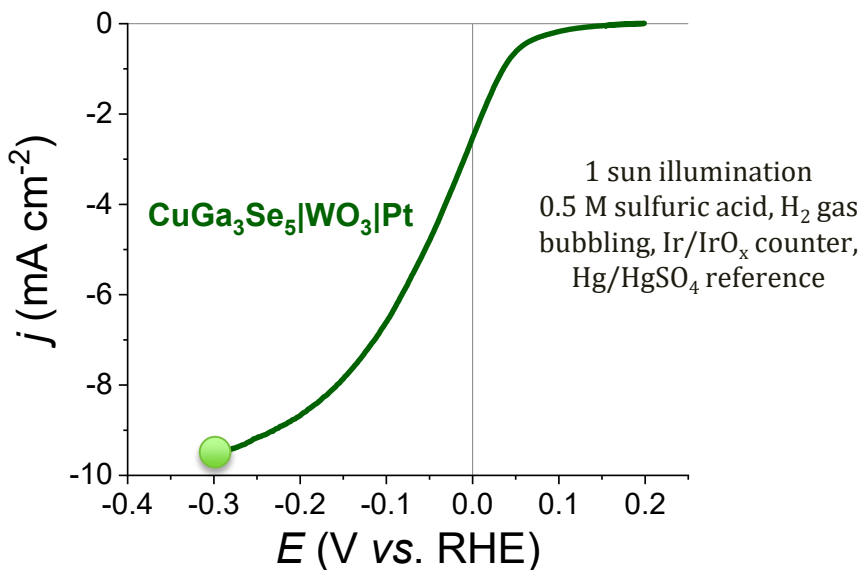
2.3) Protection against photo-corrosion (Stanford-NREL CIGSe Node)

Sample preparation

- CuGa_3Se_5 thin film co-evaporated on Mo at NREL,
- CuGa_3Se_5 sample coated at Stanford with 3.3 nm WO_3 (sputtered) coating and 1 nm Pt (e-beam evaporated) catalyst



PEC testing



→ Generate > 90% of initial photocurrent density for more than 270 h of continuous testing

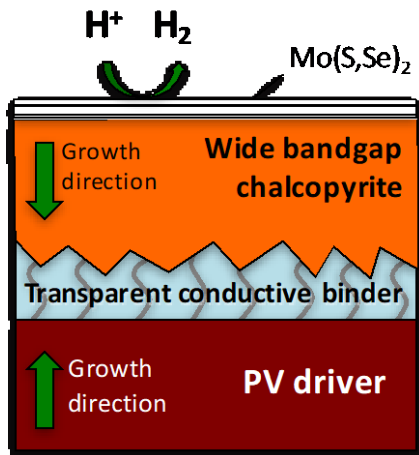


Accomplishments – Task 3: Hybrid Photoelectrode Device Integration

Device barrier (AG)

3.1) Transparent conductive (TC) binder for semi-monolithic tandem (UH)

Transparent conductive flexible composites (TCFC) to “glue” top cells onto fully integrated bottom cells



Concept image of UH's TCFC comprising conductive spheres protruding out of a polymeric film

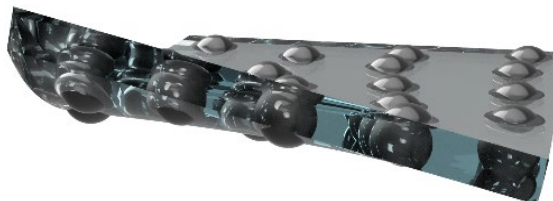
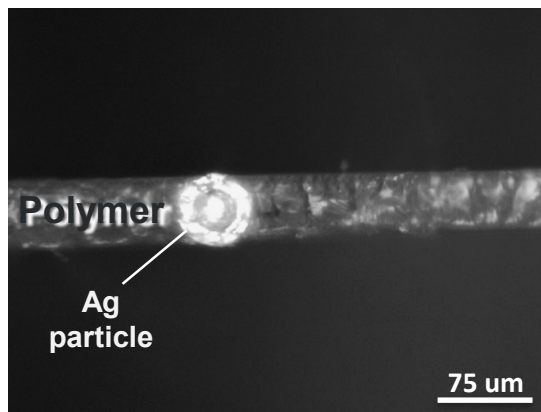


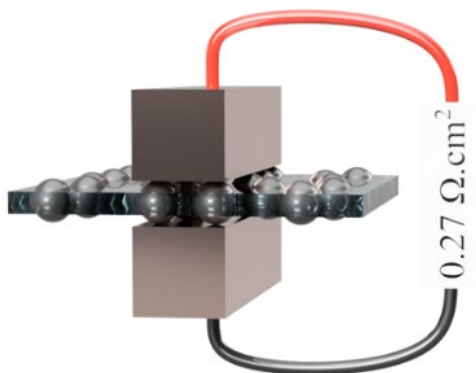
Image of UH's free-standing TCFC



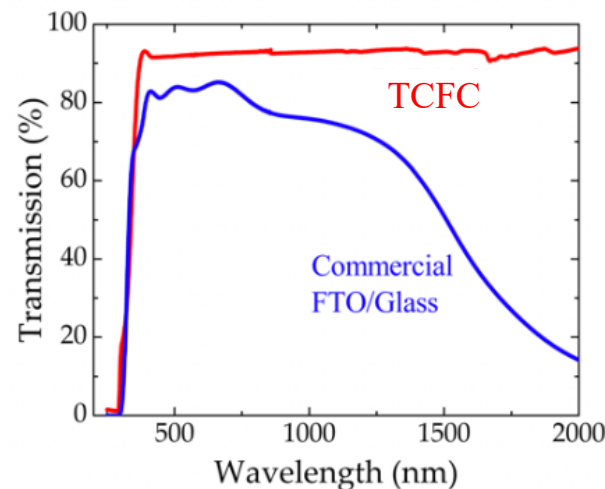
Optical cross-sectional view of TCFC



Resistance as low as 0.2 ohm.cm²



Optical transparency as high as 90%





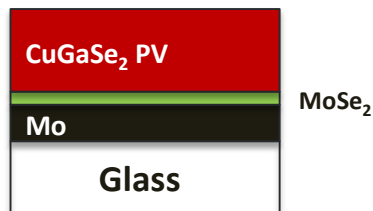
Accomplishments – Task 3: Hybrid Photoelectrode Device Integration

Device barrier (AG)

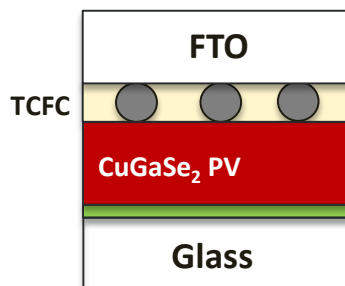
3.2) Semi-monolithic tandem integration (UH-NREL CIGSe Node)

→ Approach: semi-monolithic devices were created by exfoliating and bonding wide bandgap (1.7 eV) CuGaSe₂ solar cells onto narrow bandgap (1.1 eV) silicon devices using HNEI's transparent conductive flexible composites (TCFC).

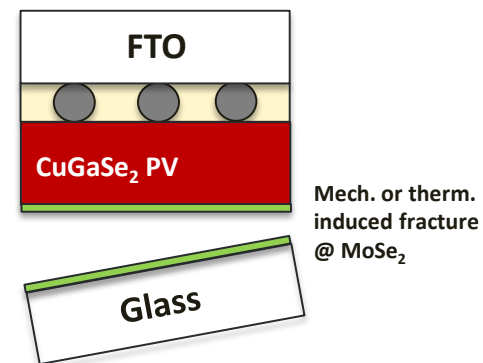
1. Top cell integration (NREL)



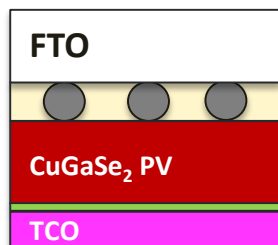
2. Bonding onto FTO handle with TCFC



3. Exfoliation

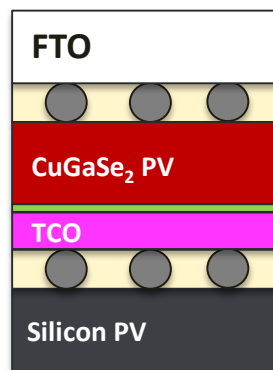


4. TCO deposition



TCO layer improves lateral charge collection

5. Final bonding onto Si bottom cell with TCFC



Our concept of semi-monolithic tandem could be extended to combine chalcopyrites with other "incompatible" low-temp. PV classes (a-Si, organic absorbers, Perovskites...etc.)

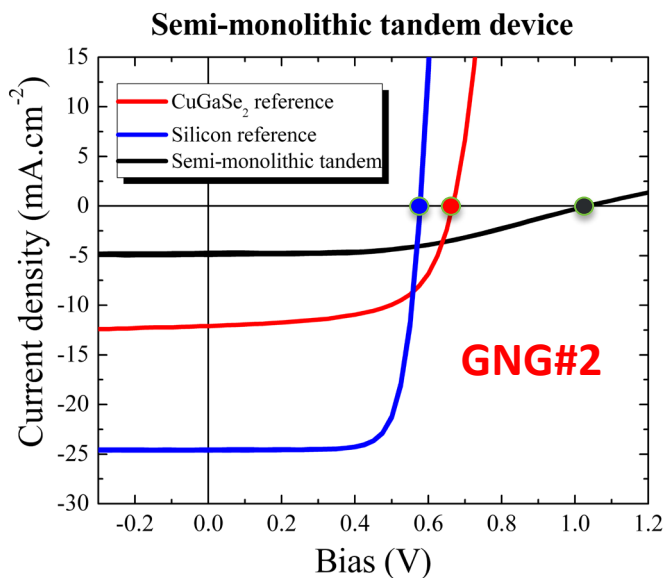
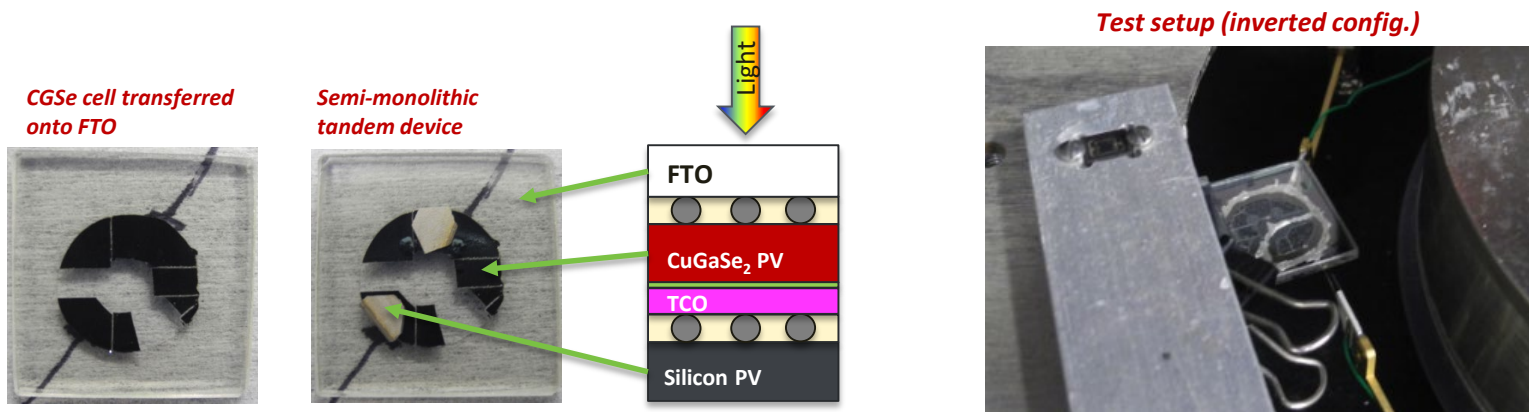


Accomplishments – Task 3: Hybrid Photoelectrode Device Integration

Device barrier (AG)

3.2) Semi-monolithic tandem integration (UH-NREL CIGSe Node)

→ Validation using NREL's 1.6 eV CuGaSe₂ device and Si solar cells.



Device	Voc (mV)
CGSe reference cell	660
Si reference cell	580
Semi-monolithic tandem	1,035

$$\frac{V_{OC-tandem}}{V_{OC-Si} + V_{OC-CGSe}} = \frac{1,035}{660 + 580} = 83\% \gg \text{GNG\#2 (50\%)}$$

- Semi-monolithic concept successfully demonstrated.
- Future work to include integration of chalcopyrites with wider bandgaps (1.8-2.0 eV).



Collaboration – Interactions with EMN project node experts to date

→ Active interactions between academic teams and EMN nodes with regular communication regarding samples exchange and collected data.

Task #	Academia-Nodes Interactions	Specific activity	Goal	Impact to Project	Barrier
1	UH - LLNL theory Node	Data exchange (XRD spectra, optical data, low temperature conductivity measurements).	Model the effect of [O] and [C] impurities on OVCs optical transmission.	This work provides guidance for novel chalcopyrite candidates selection.	AE
1	UH - NREL I-III-VI Node	Sample exchange (CuInAlSe ₂ solid state devices).	Measure photo-conversion properties of printed CuInAlSe ₂	Validates the printing method to be used to create quaternary chalcopyrites.	AE, AJ
1	UH - NREL Corrosion Node	Sample exchange (1.8eV GaInP ₂ preference photodiode).	Calibrate UH solar simulator for wide E _G chalcopyrite PEC testing	In line with benchmarking efforts, this ensure proper characterization of the proposed chalcopyrite systems.	AE
2	Stanford - NREL I-III-VI Node	Sample exchange (CuGa ₃ Se ₅).	Test WO ₃ ALD nano-coating for protection against photocorrosion.	Extend chalcopyrite photocathodes durability beyond 500 hrs (Y2 GNG #2/2).	AF
2	UH - LBNL Photophys. Node	Sample exchange (Cu-poor CuInGaS ₂).	Characterize electrical defects with photoluminescence	Identify chemical/structural defects responsible for the low photovoltage measured in some chalcopyrites.	AF
2	NREL I-III-VI Node - NREL Combinatorial Node	Sample exchange (CuGa ₃ Se ₅).	Deposition of composition graded MgZnO buffer (optimization)	Increase the photovoltage produced by chalcopyrite photocathodes (700 to 925 mV as of March 2019).	AE



Collaboration – Collaboration with cross-cutting ‘2b’ benchmarking team

- N. Gaillard, C. Heske, T. Jaramillo, T. Ogitsu and T. Deutsch have been participating in the development of PEC standards since 2008.
- Inputs for the next round of methods and protocols shared with PEC “2b benchmarking” team through the provided questionnaires.
- Participation to HydroGEN AWSM Benchmarking Meeting (organized in conjunction to ECS conference), Seattle, May 13th, 2018.
- Participation to “Advanced Water Splitting Technology Pathways Benchmarking & Protocols Workshop” held in Phoenix on October 24th & 25th 2018.
- Participation to “2nd Annual Advanced Water Splitting Technology Pathways: Benchmarking & Protocols Workshop” held in Scottsdale on October 28th & 31st 2019.

REVIEW

This section of Journal of Materials Research is reserved for papers that are reviews of literature in a given area.

Accelerating materials development for photoelectrochemical hydrogen production: Standards for methods, definitions, and reporting protocols

Zhebo Chen and Thomas F. Jaramillo^{a)}
Department of Chemical Engineering, Stanford University, Stanford, California 94305-5025

Todd G. Deutsch^{b)}
Hydrogen Technologies and Systems Center, National Renewable Energy Laboratory, Golden, Colorado 80401

Alan Kleiman-Shwarsctein
Department of Chemical Engineering, Santa Barbara, California 93106-5080

Arnold J. Forman
Department of Chemistry and Biochemistry, Santa Barbara, California 93106-5080

Nicolas Gaillard^{c)}
Hawaii Natural Energy Institute, University of Hawaii, Honolulu, Hawaii 96822

Roxanne Garland
Hydrogen, Fuel Cells and Infrastructure Technologies Program, Washington, District of Columbia 20585

Kazuhiro Takanabe
Department of Chemical System Engineering, Tokyo 113-8656, Japan

Clemens Heske
Department of Chemistry, University of California, Santa Barbara, California 93106-5080

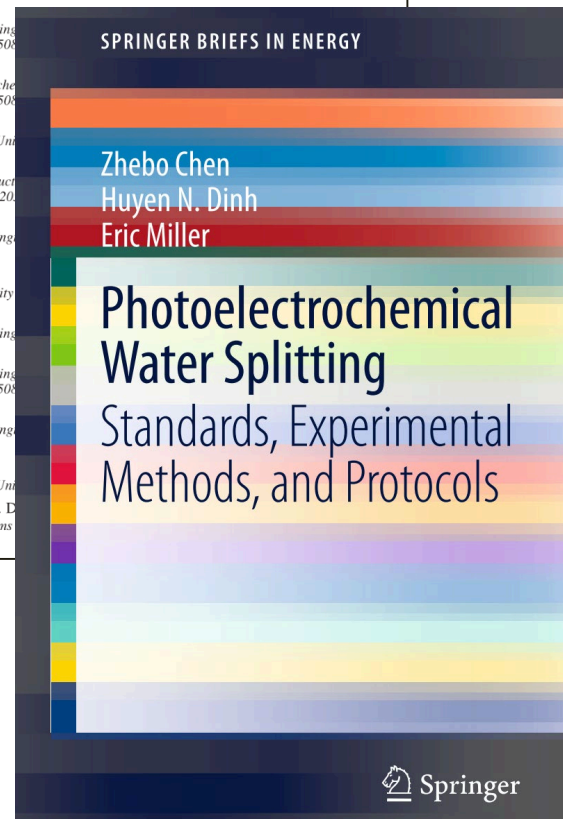
Mahendra Sunkara
Department of Chemical Engineering, University of California, Santa Barbara, California 93106-5080

Eric W. McFarland
Department of Chemical Engineering, University of California, Santa Barbara, California 93106-5080

Kazunari Domen
Department of Chemical System Engineering, Tokyo 113-8656, Japan

Eric L. Miller^{d)}
Hawaii Natural Energy Institute, University of Hawaii, Honolulu, Hawaii 96822

John A. Turner^{e)} and Huyen N. Dinh
Hydrogen Technologies and Systems Center, National Renewable Energy Laboratory, Golden, Colorado 80401





Planned Future Work^(#)

Estimated budget: ~\$410K

Task 1 - Modeling and Synthesis of Chalcopyrite Photocathodes

Sub-task 1.1 – defect passivation: with help from Theory Node (LLNL) and Photophysical Node (LBNL), further elucidate the impact of [Cu] on wide bandgap chalcopyrite sub- E_G transmission properties (e.g. Cu-rich CuGaSe_2 vs. Cu-poor CuGa_3Se_5).

Sub-task 1.2 – printed chalcopyrites: understand and solve Al segregation in $\text{Cu}(\text{In},\text{Al})\text{Se}_2$ to improve optoelectronic characteristics.

→ **IMPACT:** produce materials compatible with 20% STH efficiency or higher.

Task 2 - Interfaces Engineering for Enhanced Efficiency and Durability

Sub-task 2.1 – interface energetics: combine new surface treatments with MgZnO to create top cells with $V_{oc} > 1\text{V}$.

Sub-task 2.2 – interface durability: further improve the deposition of WO_3 protective layers and finalize milestone #3.

→ **IMPACT:** establish a path for un-assisted and durable PEC water splitting.

Task 3 - Hybrid Photoelectrode Device Integration

Sub-task 3.1 – conductive polymers: further develop the concept of conductive binder and test alternative media.

Sub-task 3.2 – semi-monolithic HPE device: pair wide bandgap chalcopyrite photocathodes with other PV drivers aiming for total photovoltage $> 1.6\text{V}$.

→ **IMPACT:** create the first efficient chalcopyrite-based tandem device.



Y3 Milestones and project deliverable table

Milestone Summary Table-Y3

Recipient Name:		University of Hawaii / Hawaii Natural Energy Institute					
Project Title:		Novel Chalcopyrites for Advanced Photoelectrochemical Water-Splitting					
Task #	Task or Subtask	Milestone Type	Milestone Number*	Milestone Description (Go/No-Go Decision Criteria)	Milestone Verification Process (What, How, Who, Where)	Anticipated Date	Anticipated Quarter
1.2	Synthesis of chalcopyrite	Milestone	1.2-3	A printed single-phase polycrystalline $\text{Cu}(\text{In,Al,B})(\text{S,Se})_2$ thin film material showing photovoltage greater than 700 mV.	Voc will be recorded at NREL via J-V analysis and reported in quarterly report	30	Q10
2.1	Interface: energetics	Milestone	2.1-3	Demonstrate an open circuit voltage greater than 1,000 mV on at least 10 MgZnO:Ga-coated wide bandgap chalcopyrite absorbers integrated on a Mo substrate under simulated AM1.5 G illumination.	Voc will be recorded at NREL via J-V analysis and reported in quarterly report	33	Q11
2.2	Interface: durability	Milestone	2.2-4	Retain 90% of metal content in a thin, transparent protective coating over the course of 300 hrs of electrocatalytic HER testing at -10 mA/cm^2 .	To be measured at Stanford via chronoamperometry	36	Q12
3	HPE integration	Project deliverable		A standalone semi-monolithic chalcopyrite-based device capable of producing renewable hydrogen with an STH efficiency of at least 5%, with a stretch goal of 10%.	To be measured at HNEI or NREL via current-voltage analysis	39	Q13



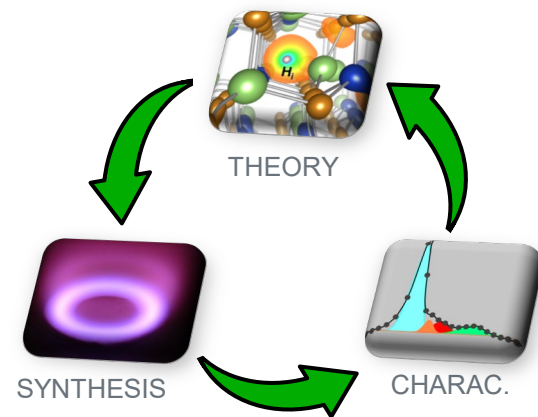
Project Summary

High-level project goal: Strengthen **theory, synthesis and advanced characterization “feedback loop”** to accelerate development of chalcopyrites for efficient PEC H₂ production.

Technical objectives:

- To address **Synthesis and Manufacturing (AJ)** and **Materials Efficiency (AE)** barriers, we model and develop new alloying and doping techniques to enhance chalcopyrites efficiency.
- To address **Materials Efficiency (AE)** and **Materials Durability (AF)** barriers, we develop new interfaces to improve chalcopyrites surface energetics and chemical stability during PEC operation.
- To address **Integrated device configuration (AG)** barrier, we develop a unique method with “transferable” PEC films to create semi-monolithic chalcopyrite-based tandems.

Benefits for HydroGEN and scientific community: our models can be used to predict the properties of future materials (optical absorption, thermodynamic stability, defect chemistry) and interfaces (band-edges offsets).



Transferable PEC thin films



Interface modelling

